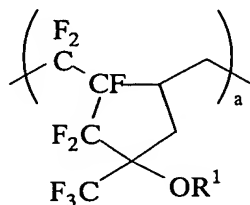
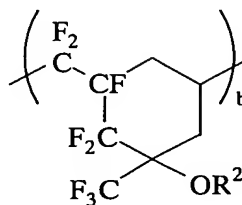


CLAIMS:

1. A resist composition comprising as the base resin a polymer comprising recurring units of the following general formulae (1a) and (1b):



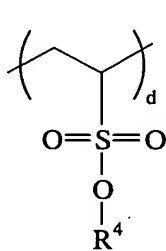
(1a)



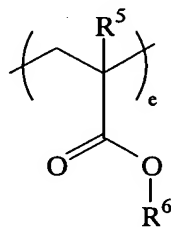
(1b)

wherein R¹ and R² each are hydrogen or an acid labile group, "a" and "b" are numbers satisfying 0 < a < 1, 0 < b < 1 and 0 < a+b ≤ 1, and another polymer comprising recurring units containing sulfonate.

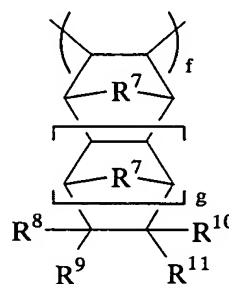
2. The resist composition of claim 1 wherein the recurring units containing sulfonate are represented by the general formulae (2a), (2b) and (2c):



(2a)



(2b)

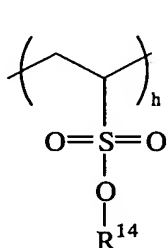


(2c)

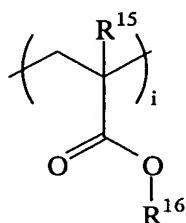
wherein R⁴ is a substituent group containing at least one fluorine atom, R⁵ is a fluorine atom or a fluorinated alkyl group having 1 to 4 carbon atoms, R⁶ is an acid labile group, R⁷ is a methylene group, oxygen atom or sulfur atom, R⁸ to R¹¹ are independently hydrogen, fluorine, -R¹²-OR¹³, -R¹²-CO₂R¹³, or a straight, branched or cyclic alkyl or fluorinated alkyl

group of 1 to 20 carbon atoms, at least one of R^8 to R^{11} contains $-R^{12}-OR^{13}$ or $-R^{12}-CO_2R^{13}$, R^{12} is a single bond or a straight, branched or cyclic alkylene or fluorinated alkylene group of 1 to 20 carbon atoms, R^{13} is hydrogen or an acid labile group, d, e, and f are numbers satisfying $0 < d < 1$, $0 \leq e < 1$, $0 \leq f < 1$, and $0 < d+e+f \leq 1$, and g is 0 or 1.

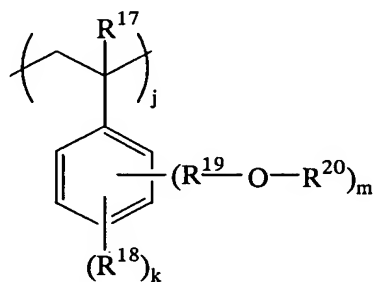
3. The resist composition of claim 1 wherein the recurring units containing sulfonate are represented by the general formulae (3a), (3b) and (3c):



(3a)



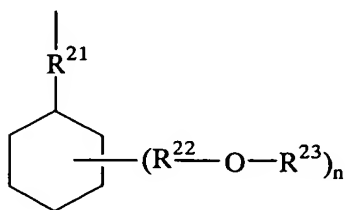
(3b)



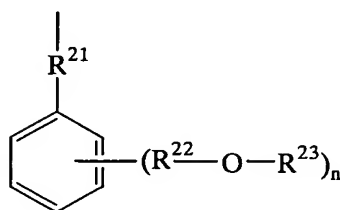
(3c)

wherein R^{14} is a substituent group containing at least one fluorine atom, R^{15} is a fluorine atom or a fluorinated alkyl group having 1 to 4 carbon atoms, R^{16} is an acid labile group, R^{17} is hydrogen, fluorine or a straight, branched or cyclic alkyl or fluorinated alkyl group of 1 to 20 carbon atoms, R^{18} is fluorine or a straight, branched or cyclic fluorinated alkyl group of 1 to 20 carbon atoms, R^{19} is a single bond or a straight, branched or cyclic alkylene or fluorinated alkylene group of 1 to 20 carbon atoms, R^{20} is hydrogen or an acid labile group, h, i, and j are numbers satisfying $0 < h < 1$, $0 \leq i < 1$, $0 \leq j < 1$, and $0 < h+i+j \leq 1$, k is an integer of 0 to 4, m is 1 or 2, and $1 \leq k+m \leq 5$.

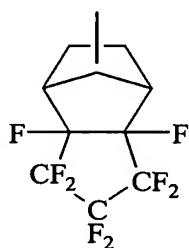
4. The resist composition of claim 2 wherein the fluorinated substituent group represented by R^4 in formula (2a) or R^{14} in formula (3a) has any of the formulae (4a) to (4e):



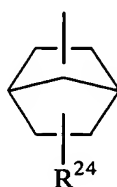
(4a)



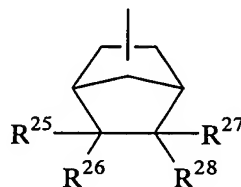
(4b)



(4c)



(4d)



(4e)

wherein R^{21} and R^{22} each are a straight, branched or cyclic fluorinated alkylene group of 1 to 20 carbon atoms, R^{23} is hydrogen or an acid labile group, R^{24} is a straight, branched or cyclic fluorinated alkyl group of 1 to 10 carbon atoms, R^{25} to R^{28} are independently hydrogen, fluorine, $-R^{29}-OR^{30}$, $-R^{29}-CO_2R^{30}$, or a straight, branched or cyclic alkyl or fluorinated alkyl group of 1 to 20 carbon atoms, at least one of R^{25} to R^{28} contains $-R^{29}-OR^{30}$ or $-R^{29}-CO_2R^{30}$, R^{29} is a single bond or a straight, branched or cyclic alkylene or fluorinated alkylene group of 1 to 20 carbon atoms, R^{30} is hydrogen or an acid labile group, and n is 1 or 2.

5. A chemically amplified positive resist composition comprising
- (A) a blend of the polymers set forth in claim 1,
 - (B) an organic solvent, and
 - 5 (C) a photoacid generator.
6. The resist composition of claim 5, further comprising
- (D) a basic compound.
- 10 7. The resist composition of claim 5, further comprising
- (E) a dissolution inhibitor.
8. A process for forming a resist pattern comprising the steps of:
- 15 applying the resist composition of claim 5 onto a substrate to form a coating,
- heat treating the coating and then exposing it to high-energy radiation in a wavelength band of 100 to 180 nm or 1 to 30 nm through a photomask, and
- 20 optionally heat treating the exposed coating and developing it with a developer.
9. The pattern forming process of claim 8 wherein the high-energy radiation is an F₂ laser beam, Ar₂ laser beam or
- 25 soft x-ray.